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MICROELECTRONICS AND RELIABILITY

Editors-in-Chief PROFESSOR N. D. STOJADINOVIĆ

Department of Microelectronics, Faculty of Electronic Engineering, University of Niš, Beogradska 14, 18000 Niš, Yugoslavia

(Tel: +381 18 49-155; Fax: +381 18 46-180; E-mail: stojadinovic@efnis.elfak.ni.ac.yu)

PROFESSOR M. G. PECHT

CALCE Electronic Packaging Research Center, University of Maryland, College Park, MD 20742, U.S.A. (Tel: +1 301 405-5323; Fax: +1 301 314-9269; E-mail: pecht@eng.umd.edu)

Regional Editors

S. C. SUN

Taiwan Semiconductor Manufacturing Co. Ltd 9 Creation Rd I Science-Based Industrial Park Hsinchu

Taiwan

Republic of China

(Tel: +886 35 781688 extn 4700; Fax: +886 35 773671; E-mail: scsun@tmsc.co.tw)

F. FANTINI

Department of Information Technology University of Parma Viale delle Scienze, 43100, Parma Italy

(Tel: +39 521 905 824; Fax: +39 521 905 822; E-mail: fausto@ee.unipr.it) H. IWAI

ULSI Device Engineering Laboratory
Microelectronics Engineering Laboratory
Toshiba Corporation
1 Komukai-Toshiba-cho, Saiwai-ku
Kawasaki 210

Kawasaki 210 Japan

(Tel: +81 44 549 2335; Fax: +81 44 549 2291; E-mail: iwai@ull.rdc.toshiba.co.jp)

D. PIERCE

Sandia Technologies Inc PO Box 23338 Albuquerque, NM 87112 U.S.A. (Tel/Fax: +1 505 271 0122;

(Tel/Fax: +1 505 271 0122, E-mail: dpiercest@aol.com)

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VOLUME CONTENTS

		Number 1
N. Stojadinović and M. Pecht	1	Editorial
H. A. Schafft, D. L. Erhart and W. K. Gladden	3	Review Papers Toward a building-in reliability approach
W. H. Krautschneider, A. Kohlhase and H. Terletzki	19	Scaling down and reliability problems of Gigabit CMOS circuits
S. Nakajima and T. Takeda	39	Failure analysis in halfmicron and quartermicron eras
M. Minondo, J. Boussey and G. Kamarinos	53	Research Papers The impact of the substrate preamorphisation on the electrical performances of p ⁺ /n silicon junction diodes
P. Francis, J. P. Colinge and D. Flandre	61	Comparison of self-heating effect in GAA and SOI MOSFETs
C. Ciofi and S. Di Pascoli	77	Temperature coefficient of resistance fluctuations during electro- migration in Al lines
L. K. J. Vandamme and A. J. van Kemenade	87	Resistance noise measurement: a better diagnostic tool to detect stress and current induced degradation
S. Graffi, G. Masetti and A. Piovaccari	95	Criteria to reduce failures induced from conveyed electromagnetic interferences on CMOS operational amplifiers
B. Lisenker and Y. Nevo	115	CMOS VLSI reliability test model
T. C. Garyet and N. Dickson	121	Improved understanding of physical defect mechanisms using fault simulation
P. M. Petković, D. P. Milovanović and V. B. Litovski	137	Symbolic fault modelling of MOS combinational circuits
E. V. Jelenkovic and K. Y. Tong	159	Technical Notes Effect of deposition conditions on stability of sputtered oxide in MOS structures
Deren Lu and Baoqing Li	171	Observation of DC currents induced in MOS capacitors during NBTS aging
JL. Loheac, F. Raoult, O. Bonnaud and M. Taurin	179	Analysis for the reliability of the intrinsic base ion implantation of a 3 GHz I ² L bipolar process from the measure of integrated resistances: from the results, setting of rules for an expert system
		Number 2

Hongzhou Wang and Hoang Pham	187	Survey of reliability and availability evaluation of complex networks using Monte Carlo techniques
B. S. Dhillon and A. R. M. Fashandi	211	Robotic systems probabilistic analysis
K. Thirusangu and K. Rangarajan	225	Marked graphs and Euler graphs
Li Jianping and Jia Xishen	237	A new partial bound enumeration technique for solving reliability redundancy optimization
S. V. Gurov, S. P. Habarov and L. V. Utkin	243	Safety analysis of a multi-phased control system

J. Malinowski and W. Preuss	255	A parallel algorithm evaluating the reliability of a system with known minimal cuts (paths)
A. Aissani	267	Limit distributions for dependent thinning of dissipative point processes
A. N. Ahmed, A. A. Soliman and S. E. Khider	277	Preservation results for ordered random variables, with applications to reliability theory
R. C. Suich	289	Reliability and cost: questions for the engineer
TL. Tran, J. S. Sherif, C. Mikulski and M. Wang	297	MY-STAR: a methodology and system for tracing and analyzing requirements
A. A. Abdel-Ghaly, G. R. Al-Dayian and F. H. Al-Kashkari	305	The use of Burr type XII distribution on software reliability growth modelling
Ying Hui Tang	315	A single-server M/G/1 queueing system subject to breakdowns—some reliability and queueing problems
A. F. Attia	323	Estimation of the reliability function using the delay-time models
G. S. Mokaddis, M. L. Tawfek and S. A. M. Elhssia	329	Analysis of a two-dissimilar unit cold standby redundant system subject to inspection and random change in units
G. S. Mokaddis, M. L. Tawfek and S. A. M. Elhssia	335	Cost analysis of a two dissimilar-unit cold standby redundant system subject to inspection and two types of repair
A. A. Hagin	341	Reliability evaluation of a repairable network with limited capacity and structural redundancy
M. M. El Fahham and H. S. El Said	349	Asymptotic expansion in the limit theorem for the convergence to Laplace distribution
A. I. Shawky	355	The single-server machine interference model with balking, reneging and an additional server for longer queues
		Technical Notes
Jun Cai and Yanhong Wu	359	A note on the preservation of the NBUC class under formation of parallel systems with dissimilar components
D. Roy	361	On classifications of multivariate life distributions in the discrete setup
	367	Book reviews
	371	Calls for papers
	377	Calendar of international conferences, symposia, lectures and meetings of interest
	379	Erratum California Cal
		Number 3
J. Fung and V. Makis	381	
o. I dily dila v. Makis	301	An inspection model with generally distributed restoration and repair times
H. Arsham	391	Goal-seeking problem in discrete event systems simulation
R. J. Burns	397	A simple technique for obtaining the MTBF of complex systems

J. Fung and V. Makis	381	repair times
H. Arsham	391	Goal-seeking problem in discrete event systems simulation
R. J. Burns	397	A simple technique for obtaining the MTBF of complex systems through numerical integration of the reliability function
W. G. Schneeweiss	403	Advanced hand calculations for fault tree analysis and synthesis
J. S. Dagpunar	417	The effect of minimal repairs on economic lot-sizing
J. N. Pan and S. L. Wu	421	Process capability analysis for non-normal relay test data
In-Kyeong Choi, Jai-Sang Koh and So-Yeon Lee	429	A symbolic reliability of multiple path required system with three states

D. Fakinos	437	The symmetric M/G/k loss system with heterogeneous servers
J. N. Pan	439	Reliability prediction of imperfect switching systems subject to multiple stresses
HZ. Huang	447	Fuzzy multi-objective optimization decision-making of reliability of series system
Cheng Kan and Wang Wen Yi	451	Preservation of some partial orderings under non-homogeneous Poisson shock model and Laplace transform
Seung Min Lee and Dong Ho Park	457	A test for the BMRL-t ₀ class
Wenyi Wang and Hongfen Zhang	461	The methods of reduction in network reliability computing
Myung B. Kong and Kyung S. Park	467	Optimal replacement of an item subject to cumulative damage under periodic inspections
P. Cappelletti, R. Bez, D. Cantarelli, D. Nahmad and L. Ravazzi	473	CAST: an electrical stress test to monitor single bit failures in flash- EEPROM structures
J. M. Nahman	483	Enumeration of minimal cuts of modified networks
D. Wilkie, R. Drwinga, E. Eichman, N. Kunnari, B. Negley and D. Richardson	487	A design of experiment analysis of serial EEPROM endurance
G. S. Mokaddis, M. L. Tawfek and S. A. M. Elhssia	493	Some characteristics of a man-machine system operating subject to different weather conditions
Yeh Lam	497	A maintenance model for two-unit redundant system
B. S. Dhillon and N. Yang	505	Comparisons of block diagram and Markov method system reliability and mean time to failure results for constant and non-constant unit failure rates
Lian-Chang Zhao and Fan-Jia Kong	511	A new formula and an algorithm for reliability analysis of networks
M. K. Radhakrishnan	519	Die attach failures related to wafer back metal processing—an AES study
E. J. Vanderperre, S. S. Makhanov and S. Suchatvejapoom	525	Long-run availability of a repairable parallel system
	529	World abstracts on microelectronics and reliability
	547	Book review

Number 4

1. Tallagisavva	543	Estimation of the degradation of amorphous silicon solar cens
H. Reiche	555	A reliability study of a small vehicle
B. S. Dhillon and N. Yang	557	Formulas for analyzing a redundant robot configuration with a built-in safety system
M. Raghavachari, A. Srinivasan and P. Sullo	565	Poisson mixture yield models for integrated circuits: a critical review
K. W. Philp and N. D. Deans	581	Comparative redundancy, an alternative to triple modular redundant system design
U. D. Kumar and M. N. Gopalan	587	Analysis of consecutive k-out-of-n: F systems with single repair facility
Fang-Ming Shao and Lian-Chang Zhao	591	Optimal design improving a communication network reliability
M. V. Koutras	597	Consecutive-k,r-out-of-n: DFM systems

Volume Contents

**		Totalia Contents
M. A. EI-Damcese	605	System reliability with common-cause hazard to obey an exponential power model
M. T. Abuelma'atti and I. S. Qambar	609	SPICE application in the study of the behaviour of multi-state systems described by Markov models
Yeh Lam	615	An optimal maintenance model using a number of different actions
M. A. W. Mahmoud and M. E. Moshref	623	Probabilistic analysis of a two-unit cold standby redundant system subject to failure of controlled weather device
Lian-Chang Zhao and Fang-Ming Shao	629	Optimization of connecting two communication networks subject to a reliability constraint
Yi-Chih Hsieh	635	Optimal assignment of priorities for the machine interference problems
G. S. Mokaddis, S. W. Labib and A. M. Ahmed	641	Analysis of a two-unit warm standby system subject to degradation
A. Bouhdada, S. Bakkali and A. Touhami	649	Modelling of gate-induced drain leakage in relation to technological parameters and temperature
Jae-Hak Lim and Jai-Sang Koh	653	Reliability analysis and comparison of several structures
V. Ramachandran, V. Sivakumar, K. Sathiyanarayanan and S. Chandrasekaran	661	Technical Notes Genetics based redundancy optimization
V. Ramachandran, J. Kannan, K. Sathiyanarayanan and V. Sivakumar	665	Optimal replacement strategies—genetic algorithms approach
V. Sridharan and P. Mohanavadivu	669	Optimum interchangement time for a two-dissimilar-unit with two types of repairman
S. Dey and P. Sarmah	673	Estimation of parameters of a model of a complex repairable system
A. Rekha and T. Shyam Sunder	677	Survival function of a component under random strength attenuation
A. Rekha and T. Shyam Sunder	683	Reliability of a cascade system with exponential strength and gamma stress
	687	World abstracts on microelectronics and reliability
H. Reiche	711	Things are changing—a report on the Reliability and Maintainability Symposium 1996
		Number 5

T. Puritis	713	Problems related to the avalanche and secondary breakdown of silicon p-n junction
O. Chryssaphinou, S. Papastavridis and T. Tsapelas	721	A generalized multi-standby multi-failure mode system with various repair facilities
Sung-Jae Cho and Kyung-Chang Kim	725	Recovery technique in a client-server main memory DB environ- ment
N. P. Padhy, S. R. Paranjothi and V. Ramachandran	733	A hybrid fuzzy neural network-expert system for a short term unit commitment problem
E. J. Vanderperre, S. Vannakrairojn and S. S. Makhanov	739	A delay-differential equation related to a renewable parallel system
V. Sridharan and P. R. Jayashree	743	Transient behaviour for a continuous time parameter system with finite waiting room

V. Sridharan and P. Mohanavadivu	747	Reliability and availability analysis for two non-identical unit parallel systems with common cause failures and human errors
A. A. Ismaeel and R. Bhatnagar	753	Power-constrained testing for bridging and stuck short faults in CMOS combinational circuits
A. A. Ismaeel, R. Bhatnagar and M. Khan	763	Modeling for bridging faults in nMOS combinational circuits
L. V. Utkin, S. V. Gurov and I. B. Shubinsky	779	Reliability of systems by mixture forms of uncertainty
V. N. Rayapati and B. Kaminska	785	Dynamic reconfiguration schemes for megabit BiCMOS SRAMs and performance evaluation
N. Arora and D. Kumar	795	Availability analysis of steam and power generation systems in the thermal power plant
S. V. Gurov and L. V. Utkin	801	Reliability and optimization of systems with periodic modifications in the probability and possibility contexts
M. A. Aziz	809	Technical Notes Pathset enumeration of directed graphs by the set theoretic method
A. Chaturvedi	815	A note on sequential point estimation of the mean of a gamma population
N. Arora and D. Kumar	819	Stochastic analysis and maintenance planning of the ash handling system in the thermal power plant
B. N. Pandey and O. Rai	825	Shrinkage testimation of the shape parameter of an inverse Gaussian distribution using a $(\alpha\beta)_{\min}$ test
S. P. Rajamanickam and B. Chandrasekar	829	Reliability measures for two-unit systems with a dependent structure for failure and repair times
V. Sridharan and P. Mohanavadivu	835	A note on the cost analysis of an <i>n</i> -unit system with spares
S. A. H. Rizvi and R. K. Singh	841	On estimation of population mean using known coefficient of variation
R. Gupta, S. Z. Mumtaz and R. Goel	845	A two dissimilar unit multi-component system with correlated failures and repairs
R. Gupta, Ramkishan and R. Goel	851	Analysis of a system having super-priority, priority and ordinary units with arbitrary distributions
M. Jacob, S. Narmada and T. Varghese	857	Analysis of a two unit deteriorating standby system with repair
H. P. Singh and R. Singh	863	A class of shrinkage estimators for the variance of a normal population
S. Somasundaram and D. A. M. Dhas	869	Reliability of a dynamic <i>n</i> -unit shared load parallel system under different failure times
	873	Book reviews
		Number 6
M Meniconi D M Barry	975	Variations in performance degradation of CMOS NAND gates due

M. Meniconi, D. M. Barry and D. C. Betts	875	Variations in performance degradation of CMOS NAND gates due to ionizing radiation
A. Kleyner, S. Bhagath, M. Gasparini, J. Robinson and M. Bender	879	Bayesian techniques to reduce the sample size in automotive electronics attribute testing
C. R. Tripathy, R. N. Mahapatra and R. B. Misra	885	Reliability analysis of hypercube multicomputers
Yisong Dai	893	A precision noise measurement and analysis method used to estimate reliability of semiconductor devices

Volume Contents

B. Burtschy, G. Albeanu, D. N. Boros, F. Popentiu and V. Nicola	901	Improving software reliability forecasting
T. Satow and T. Nakagawa	909	Three replacement models with two kinds of damage
I. J. Jóźwiak	915	An introduction to the studies of reliability of systems using the Weibull proportional hazards model
Zhang Honfeng and Wang Wen Yi	919	The NBEFR and NWEFR classes of life distributions
R. K. Paul and Md. Borhan Uddin	923	Estimation of reliability of stress-strength model with non-identical component strengths
M. Jain	929	Research Notes An (m, M) machine repair problem with spares and state dependent rates: a diffusion process approach
S. A. Siddiqui, S. Jain and R. K. Chauhan	935	Bayesian analysis of reliability and hazard rate function of a mixture model
A. Chaturvedi	943	Further remarks on sequential estimation of a scale parameter in exponential distributions with an unknown location
S. Kumar, N. P. Mehta and D. Kumar	949	Steady state behaviour and maintenance planning of a desulphurization system in a urea fertilizer plant
D. Pandey, S. K. Tyagi and S. Tyagi	955	Reliability analysis of star type local area networks
C. Tripathy	961	Microprocessor based recognition of dot-matrix characters using a fibre-optic scanner
P. Chandrasekhar and R. Natarajan	969	Confidence limits for steady state availability of systems with lognormal operating time and inverse Gaussian repair time
	973	Book reviews
	977	Calls for papers
	981	Calendar of forthcoming events

Number 7

SPECIAL ISSUE

RELIABILITY F	PHYSICS O	F ADVANCED ELECTRON DEVICES
N. Stojadinović	983	Editorial
	INTRO	DDUCTORY REVIEW
E. Takeda	985	Challenges for giga-scale integration
		HOT CARRIERS
S. Cristoloveanu	1003	Hot-carrier degradation mechanisms in silicon-on-insulator MOS-FETS
E. Simoen and C. Claeys	1015	Hot-carrier stress effects on the amplitude of random telegraph signals in small area Si p-MOSFETS
R. Ghodsi and Y. T. Yeow	1021	Small-signal gate-to-drain capacitance of MOSFET as a diagnostic tool for hot-carrier induced degradation
	OXI	DE BREAKDOWN
D. J. Dumin	1029	Characterizing wearout, breakdown and trap generation in thin silicon oxide
E. Atanassova	1039	Thin oxide MOS damage generated after treatment in a MERIE

reactor

A. Martin, P. O'Sullivan and A. Mathewson	1045	Study of unipolar pulsed ramp and combined ramped/constant voltage stress on MOS gate oxides
	ELE	CTROMIGRATION
D. G. Pierce and P. G. Brusius	1053	Electromigration: a review
J. L. Gonzalez and A. Rubio	1073	Shape effect on electromigration in VLSI interconnects
C. Ciofi, M. Franzese and B. Neri	1079	Characterization of Al–Si–Cu metal lines by means of TEM analysis and the SARF technique
		ESD
W. R. Anderson	1087	Circuit and process design considerations for ESD protection in advanced CMOS processes
S. Daniel, JW. Kim, KD. Hong and CK. Yoon	1105	ESD tester parasitics and stress conditions and their impact on device failure levels and failure mechanisms
R. Fried, Y. Blecher and S. Friedman	1111	Structures for ESD protection in CMOS processes
	CON	MPOUND DEVICES
G. Meneghesso, E. De Bortoli, D. Sala and E. Zanoni	1121	Failure mechanisms of AlGaAs/InGaAs pseudomorphic HEMT's: effects due to hot electrons and modulation of trapped charge
P. Cova, R. Menozzi, F. Fantini, M. Pavesi and G. Meneghesso	1131	A study of hot-electron degradation effects in pseudomorphic HEMTs
V. A. Vaschenko, V. F. Sinkevitch and Y. B. Martynov	1137	Physical limitation on drain voltage of power PM HEMT
	RE	ESEARCH NOTES
S. Dimitrijev, P. Tanner, ZQiang Yao and H. B. Harrison	1143	Slow state characterization by measurements of current-voltage characteristics of MOS capacitors
Z. Savić	1147	A method for separating the effects of interface from border and oxide trapped charge densities in MOS transistors
	1151	List of reviewers
	1153	Calendar of forthcoming events

Number 8

J. Nahman	1161	Fuzzy logic based network reliability evaluation
M. T. Madi	1165	Bayesian inference for partially accelerated life tests using Gibbs sampling
A. M. Sultan	1169	New approximation for parameters of normal distribution using type II-censored sampling
M. A. El-Damcese	1173	Suggested procedure for preventive maintenance policy
J. Lee	1179	Reliability models of a class of self-healing rings
K. Hiraoka and T. Nikaido	1185	Reliability design of current stress in LSI interconnects using the estimation of failure rate due to electromigration
P. K. K. Loh and A. Wahab	1193	A fault-tolerant communications switch prototype
Quey-Jen Yeh, TP. Chang and HC. Chang	1197	An inventory control model with Gamma distribution
Quan-Lin Li, De-Ju Xu and Jinhua Cao	1203	Reliability approximation of a Markov queueing system with server breakdown and repair

Ming-Che Lu and Dong Shang Chang Bootstrap prediction intervals for the Birnbaum-Saunders distri-1213 Bounds for reliability of k-within connected-(r,s)-out-of-(m,n)F. S. Makri and Z. M. Psillakis 1217 failure systems Reliability analysis of a $M_1^{X_1}$, $M_2^{X_2}/G_1$, $G_2/1$ queueing system with a **Dequan Yue and Jinhua Cao** 1225 repairable service station On a two-dissimilar-unit system with three modes and random Su Baohe 1233 check Estimation of the degradation of InGaN/AlGaN blue light-emitting T. Yanagisawa 1239 K. Thirusangu and K. Rangarajan 1243 Marked graphs and Hamiltonian graphs Zhi-Bin Tan 1251 Reliability and availability analysis of two-unit warm standby microcomputer systems with self-reset function and repair facility J. Malinowski and W. Preuss 1255 Reliability of a two-way circular consecutively connected system with multistate components S. A. Metwally 1259 Three-phase queueing servicing system with renewable servers Research Notes A. Noore 1267 Fault location in multi-modular redundant systems C. K. Goel, S. Narmada and M. Jacob 1271 Analysis of a two-unit system with connecting and disconnecting effect 1275 World abstracts on microelectronics and reliability 1293 Calendar of forthcoming events

Number 9

SPECIAL ISSUE ADVANCES IN MICROELECTRONICS: APPROACHING THE MILLENIUM

A. Shah and P. Yang	1301	MOS technology: trends and challenges in the ULSI era
WH. Lee	1309	MOS device structure development for ULSI: low power/high speed operation
T. Ohmi and T. Shibata	1315	Intelligence implementation on silicon based on four-terminal device electronics
W. Joppich and S. Mijalković	1329	Recent advances and trends in numerical techniques for process simulation
F. Balestra and S. Cristoloveanu	1341	Special mechanisms in thin-film SOI MOSFETs
G. Ghibaudo and F. Balestra	1353	Low temperature characterization of silicon CMOS devices
I. N. Shvetzov-Shilovsky	1367	MOSFET prediction in space environments
P. Rossel, H. Tranduc and G. Charitat	1375	Power MOS devices: structure evolutions and modelling approaches
H. Tadano, M. Ishiko, S. Kawaji and Y. Taga	1389	Low loss static induction devices (transistors and thyristors)
H. L. Hartnagel	1397	Microelectronics based on compound semiconductors
R. S. Popovic and J. A. Flanagan	1401	Sensor microsystems
V. Liberali, S. Brigati, F. Francesconi and F. Maloberti	1411	Progress in high-speed and high-resolution CMOS data converters

Number 10/11

SPECIAL ISSUE

8th European Symposium on RELIABILITY OF ELECTRON DEVICES, FAILURE PHYSICS AND ANALYSIS (ESREF 97)

Editorial N. Labat and A. Touboul	ix
the state of the s	
THEME A: BUILDING-IN QUALITY AND RELIABILITY	
Diagnostic technique for projecting gate oxide reliability and device reliability J. T. Park, D. N. Ha, C. G. Yu, B. G. Park and J. D. Lee	1421
Building-in reliability during library development: hot-carrier degradation is no longer a problem of the technologists only! R. Bellens, I. Clemminck and K. van Doorselaer	1425
A new reliability prediction model for telecommunication hardware M. Nilsson and Ö. Hallberg	1429
Lifetime prediction for PMOS and NMOS devices based on a degradation model for <u>Gate-Bias-Stress</u> A. Narr and A. Lill	1433
Direct parameter extraction for hot-carrier reliability simulation S. Minehane, S. Healy, P. O'Sullivan, K. McCarthy, A. Mathewson and B. Mason	1437
An on-wafer test structure to measure the effect of thermally-induced stress on silicon devices Y. Haddab, D. Manic and R. S. Popovic	1441
Computer-based training for failure analysis C. Henderson	1445
An other way to assess electronics part reliability P. Charpenel, P. Cavernes, J. Borowski and J. M. Chopin	1449
THEME B: MODELLING OF FAILURE MECHANISMS	
ESD	
ESD characteristics of a lateral NPN protection device in epitaxial and non-epitaxial substrates T. Suzuki, S. Ito and H. Monma	1453
Using an SCR as ESD protection without latch-up danger G. Notermans, F. Kuper and JM. Luchies	1461
Improving the ESD performance of input protection circuits in retrograde well and TI structures YK. Park, TH. Kang, CH. Choi, JT. Kong and SH. Lee	1457
Dangerous parasitics of socketed CDM ESD testers H. Gossner and T. Brodbeck	1465
Electromigration	
Reliability challenges for deep submicron interconnects J. W. McPherson, H. A. Le and C. D. Graas	1469
Are high resolution resistometric methods really useful for the early detection of electromigration damage? A. Scorzoni, S. Franceschini, R. Balboni, M. Impronta, I. de Munari and F. Fantini	1479
The thermally balanced bridge technique (TBBT): a new high resolution resistometric measurement technique for the study of electromigration-induced early resistance changes in metal stripes J. van Olmen, W. de Ceuninck, L. de Schepper, A. Goldoni, A. Cervini and F. Fantini	1483
Influence of ARC capping layer on stress induced voiding in narrow AlCu metallisations L. Arnaud, D. Mariolle, P. Moreau and L. Ulmer	1487
Early resistance change and stress/electromigration modeling in aluminum interconnects V. Petrescu, A. J. Mouthaan and W. Schoenmaker	1491
Temperature and thermal conductivity modes of scanning probe microscopy for electromigration studies A. Buck, B. K. Jones and H. M. Pollock	1495

Oxide and MOS Devices Dielectric reliability in deep-submicron technologies: from thin to ultrathin oxides 1499 E. Vincent, S. Buyere, C. Papadas and P. Mortini Activation of parasitic bipolar transistor during reverse recovery of MOSFET's intrinsic diode 1507 G. Busatto, G. V. Persiano, A. G. M. Strollo and P. Spirito 1511 Characteristics of intrinsic breakdown of thin reoxidized nitride for trench capacitors E. Wu, C. Hwang, R. Vollertsen, R. Kleinhenz and A. Strong Analysis of the evolution of the trapped charge distributions in 10nm SiO₂ films during DC and bipolar dynamic 1517 R. Rodriguez, M. Nafria, J. Suñe and X. Aymerich Oxide thickness dependence of nitridation effects on TDDB characteristics 1521 M. K. Mazumder, A. Teramoto, M. Katsumata, M. Sekine, S. Kawazu and H. Koyama Transient stressing and transient characterization of thin tunnel oxides 1525 M. Ciappa, A. Naitana and M. Vanzi Investigation of stress induced leakage current in CMOS structures with ultra-thin gate dielectrics 1529 C. Jahan, K. Barla and G. Ghibaudo A high resolution method for measuring hot carrier degradation in matched transistor pairs 1533 R. Dreesen, W. de Ceuninck, L. de Schepper and G. Groeseneken Modelling of Failure Mechanisms Comparison of different on-chip ESD protection structures in a 0.35 μm CMOS technology 1537 C. Richier, N. Maene, G. Mabboux and R. Bellens Gate and circuit level analysis of N-type SRAM reliability failures 1541 K. Symonds, J. Wilson, P. Lindo and M. Bahrami A study of the thermal, electrical and mechanical influence on degradation in an aluminumpad structure 1545 X. Yu and K. Weide Investigations of stress distributions in tungsten-filled via structures using finite element analysis 1549 J. Coughlan, S. Foley and A. Mathewson Influence of thermal heating effect on pulsed DC electromigration 1553 P. Waltz, L. Arnaud, G. Tartavel and G. Lormand Microstructural and surface effects on electromigration failure mechanism in Cu interconnects 1557 A. Gladkikh, M. Karpovski and A. Palevski Effects of ESD protections on latch-up sensitivity of CMOS 4-stripe structures 1561 P. Pavan, A. Pellesi, G. Meneghesso and E. Zanoni THEME C: TECHNIQUES AND METHODS FOR DEVICE ANALYSIS **Electron and Optical Beam Testing** Automated placement of testing pads for electron-beam observation 1565 N. Kuji and T. Takeda Dual phase probing technique for IC-internal failure analysis 1569 S. Görlich, O. Ritschel, N. Webster and A. Winterstein MMIC in-circuit and in-device testing with an on-wafer high frequency electric force microscope test system 1575 A. Leyk, S. van Waasen, F. J. Tegude and E. Kubalek Absolute quantitative time resolved voltage measurements on 1 µm conducting lines of integrated circuits via 1579 electric force microscope-(EFM-) testing J. Bangert and E. Kubalek Characterization of thermal device properties with nanometer resolution 1583 R. M. Cramer, L. Bruchhaus and L. J. Balk High sensitivity and high resolution differential interferometer: micrometric polariscope for thermomechanical 1587 studies in microelectronics

S. Dilhaire, T. Phan, E. Schaub and W. Claeys

A reliability study of titanium silicide lines using micro-Raman spectroscopy and emission microscopy

I. de Wolf, D. J. Howard, M. Rasras, A. Lauwers, K. Maex, G. Groeseneken and H. E. Maes

1591

Volume Contents	XIII
Modification and application of an emission microscope for continous wavelength spectroscopy M. Rasras, I. de Wolf, G. Groeseneken and H. E. Maes	1595
Noise Analysis	
Low frequency noise characterization of 0.18 μm Si CMOS transistors T. Boutchacha, G. Ghibaudo, G. Guégan and T. Skotnicki	1599
Retarding effect of surface base compensation on degration of noise characteristics of BiCMOS BJTs P. Llinares, S. Niel, G. Ghibaudo, L. Vendrame and J. A. Chroboczek	1603
Comments on the utilization of noise measurements for the characterization of electromigration in metal lines C. Ciofi, V. Dattilo and B. Neri	1607
Techniques and Methods for Device Analysis	
Layers decoration on FIB cross-sections G. Perez, F. Courtade, B. Benteo and J. Lin-Kwan	1611
Three-dimensional analysis for multilayer wiring in sub-half-micron devices N. Murata, Y. Hirose, K. Maekawa, M. Ikeno and H. Koyama	1615
New methodology for localizing faults in programmable and commercial circuits R. Desplats, P. Perdu, F. Marc, Y. Danto and P. Welby	1619
Micro-extraction spectrometers for voltage contrast in the SEM A. R. Dinnis and A. K. Dinnis	1623
Effect of tip shape in the design of long distance electrostatic force microscopy S. Belaidi, P. Girard and G. Leveque	1627
Applications of scanning electrical force microscopy F. Müller, AD. Müller, M. Hietschold and S. Kämmer	1631
Noise and DC characteristics of power silicon diodes R. Crook and B. K. Jones	1635
In situ ageing, a development of the in situ techniques for building-in reliability L. Galateanu	1639
THEME D: III-V DEVICES	
Failure mechanism and SPICE modeling of AlGaAs/GaAs HBT long-term current instability J. J. Liou and S. H. Sheu	1643
GaAs power MMIC: a design methodology for reliability J. L. Muraro, F. Coppel, G. Gregoris, P. G. Tizien, J. L. Roux, J. Graffeuil and R. Plana	1651
In-situ study of the degradation behaviour of GaAs MESFETS for HI-REL applications R. Petersen, W. de Ceuninck, L. de Schepper and G. Gregoris	1655
Reliability study on three-dimensional Au/WSiN interconnections for ultra-compact MMICs H. Sugahara, M. Kimizuka, Y. K. Fukai, M. Hirano and F. Hyuga	1659
Thermal simulation and characterisation of the reliability of THz Schottky diodes M. Brandt, M. Schüßler, E. Parmeggiani, C. I. Lin, A. Simon and H. L. Hartnagel	1663
Finite element method applied to stress simulation of high power 980nm pump lasers M. Manna, F. Magistrali, M. Maini and D. Reichenbach	1667
SiC-diodes forward surge current failure mechanisms: experiment and simulation A. Udal and E. Velmre	1671
Analysis of hot electron degradations in pseudomorphic HEMTs by DCTS and LF noise characterization N. Labat, N. Saysset, A. Touboul, Y. Danto, P. Cova and F. Fantini	1675
Development of "kink" in the output I-V characteristics of pseudomorphic HEMT's after hot-electron accelerated testing	1679
G. Meneghesso, B. Cogliati, G. Donzelli, D. Sala and E. Zanoni	
Impact of InP HEMT epilayer designs on side gating effects C. Berthelemot, P. Vigier, J. M. Dumas and J. C. Harmand	1683
An investigation into electrical parameter settling times of GaAs FETs and MMICs F. Coppel, J. M. Dumas and J. L. Cazaux	1687

Characterisation of degradation mechanisms in resonant tunnelling diodes A. Vogt, M. Brandt, A. Sigurdardottir, M. Schüssler, D. Peña, A. Simon, H. L. Hartnagel, M. Rodewald, M. Roesner, H. Fuess, S. N. N. Goswami and K. Lal	1691
An automatic adaptation method for heterojunction bipolar transistor dynamic test S. Gauffre, G. Duchamp, L. Casadebaig, J. Pistre and A. Cazarre	1695
Failure mechanisms of GaAs MESFETS with Cu/refractory metallized gates T. Feng, A. Dimoulas, A. Christou, G. Constantinidis and Z. Hatsopoulos	1699
Bias stress reliability of Be-, Zn- and C-doped base microwave HBTs A. A. Rezazadeh, T. Ahmad and M. A. Crouch	1703
Experimental analysis and 2D simulation of AlGaAs/GaAs HBT base leakage current C. Maneux, N. Labat, N. Saysset, A. Touboul and Y. Danto	1707
THEME E: POWER DEVICES	
Cosmic ray induced failures in high power semiconductor devices H. R. Zeller	1711
Substrate-to-base solder joint reliability in high power IGBT modules E. Herr, T. Frey, R. Schlegel, A. Stuck and R. Zehringer	1719
Reliability issues in 650V high voltage bipolar-CMOS-DMOS integrated circuits J. A. van der Pol, H. J. Gerritsen, R. T. H. Rongen, P. P. M. C. Groeneveld, P. W. Ragay and H. A. van den Hurk	1723
A laser beam method for evaluation of thermal time constant in smart power devices N. Seliger, D. Pogany, C. Fürböck, P. Habaš, E. Gornik and M. Stoisiek	1727
Thermal characterization of IGBT power modules P. Cova, M. Ciappa, G. Franceschini, P. Malberti and F. Fantini	1731
Reliability of smart power devices B. Murari	1735
Suppressing the parasitic bipolar action of SOI-MOSFETs by using back-side bias-temperature treatment H. Koizumi, M. Shimaya and T. Tsuchiya	1743
New understanding of LDD NMOS hot-carrier degradation and device lifetime at cryogenic temperatures J. Wang-Ratkovic, R. C. Lacoe, K. MacWilliams, M. Song, S. Brown and G. Yabiku	1747
Effects of current density and chip temperature distribution on lifetime of high power IGST modules in traction working conditions A. Hamidi and G. Coquery	1755
High-temperature-reverse-bias testing of power VDMOS transistors N. Tošić, B. Pešić and N. Stojadinović	1759
Dielectric testing for integrated power devices S. Oussalah and R. Jerisian	1763
Bias temperature reliability of p-channel high-voltage devices A. Demesmaeker, A. Pergoot and P. de Pauw	1767
THEME F: PACKAGING AND INTERCONNECTIONS	
High performance microsystem packaging: a perspective A. D. Romig Jr, P. V. Dressendorfer and D. W. Palmer	1771
Mechanical response of solder joints in flip-chip type structures A. Soper, G. Pozza, M. Ignat and G. Parat	1783
Ultrasonic images interpretation improvement for microassembling technologies characterisation L. Bechou, Y. Ousten, B. Tregon, F. Marc, Y. Danto, R. Even and P. Kertesz	1787
Micromachined structure reliability testing specificity. The Motorola MGS1100 gas sensor example J. M. Bosc and J. P. Odile	1791
Evaluation of stresses in packaged ICs by in situ measurements with an assembly test chip and simulation C. Ducos, E. Saint Christophe, H. Frémont, G. N'Kaoua, C. Pellet and Y. Danto	1795
Author Index	

Number 12

R. Billinton and H. Chen 1799 Weaknesses of the conventional three-state model in stationoriented reliability evaluation E. De Baetselier, W. Goedertier 1805 A survey of the thermal stability of an active heat sink and G. De Mey W. De Ceuninck, J. Manca, 1813 Design of a new test structure for the study of electromigration with V. D'Haeger, J. Van Olmen, early resistance change measurements L. De Schepper and L. M. Stals R. R. Kamath and P. F. Mead 1817 Procedure for evaluation of thermal management requirements in a laser diode structure G. A. Allan and A. J. Walton 1825 Efficient critical area measurements of IC layout applied to quality and reliability enhancement D. J. Hauck and J. B. Keats 1835 Robustness of the exponential sequential probability ratio test (SPRT) when Weibull distributed failures are transformed using a "known" shape parameter K. Nikawa and S. Inoue 1841 LSI failure analysis using focused laser beam heating Research Notes A. J. Watkins 1849 A note on expected Fisher information for the Burr XII distribution W. L. Pearn and K. S. Chen 1853 Capability indices for non-normal distributions with an application in electrolytic capacitor manufacturing K.-W. Chen and A. S. Papadopoulos 1859 Shortest Bayes credibility intervals for the lognormal failure model World abstracts on microelectronics and reliability 1883 Calendar of forthcoming events